UMH14NFHA / IMH14AFRA

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Datasheet

AEC-Q101 Qualified

Parameter	Tr1 and Tr2
$V_{\sf CEO}$	50V
I _C	100mA
R_1	47kΩ

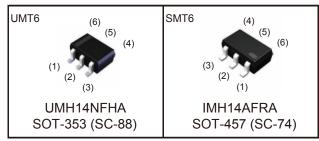
Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC144T chips in one package.
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

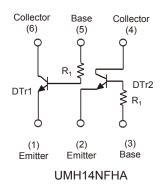
Application

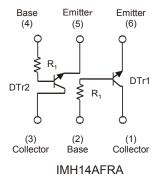
Inverter circuit, Interface circuit, Driver circuit

Outline



•Inner circuit





Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
UMH14NFHA	UMT6	2021	TR	180	8	3,000	H14
IMH14AFRA	SMT6	2928	T108	180	8	3,000	H14

● Absolute maximum ratings (Ta = 25°C)

<For DTr1 and DTr2 in common>

Parameter		Symbol	Values	Unit
Collector-base voltage		V_{CBO}	50	V
Collector-emitter voltage		V _{CEO}	50	V
Emitter-base voltage		V_{EBO}	5	V
Collector current		I _C ^{*1}	100	mA
Collector Power dissipation UMH14NFHA IMH14AFRA		P _D *2	150 (Total) ^{*3}	mW
		FD FD	300 (Total)*4	mW
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	−55 to +150	°C

●Electrical characteristics(Ta = 25°C)

<For DTr1 and DTr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 50μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	0.5	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	0.5	μА
Collector-emitter saturation voltage	V _{CE(sat)}	I _C / I _B = 10mA / 1mA	-	-	0.3	V
DC current gain	h _{FE}	V_{CE} = 5V , I_{C} = 1mA	100	250	600	-
Input resistance	R ₁	-	32.9	47	61.1	kΩ
Transition frequency	f _T *1	$V_{CE} = 10V, I_{E} = -5mA$ f = 100MHz	-	250	-	MHz

^{*1} Characteristics of built-in transistor

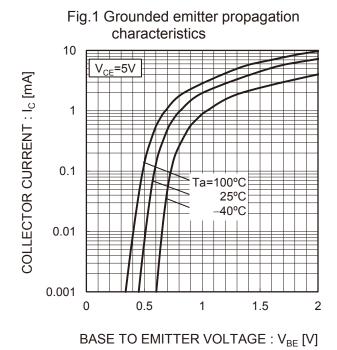
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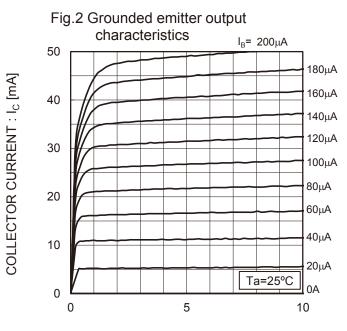
^{*2} Each terminal mounted on a reference footprint

^{*3 120}mW per element must not be exceeded.

^{*4 200}mW per element must not be exceeded.

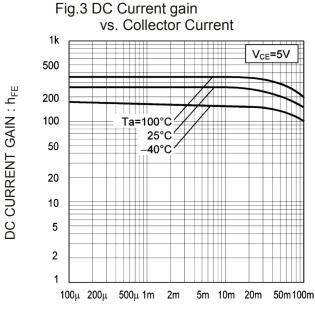
●Electrical characteristic curves (Ta = 25°C) <For DTr1 and DTr2 in common>





COLLECTOR TO EMITTER VOLTAGE: V_{CE} [V]

Fig.4 Collector-emitter saturation voltage



vs. Collector Current $I_C/I_B=10$ 500m COLLECTOR SATURATION VOLTAGE: V_{CE(sat)} [V] 200m Ta=100°C 100m 25°C 50m 40°C 20m 10m 5m 2m 100μ 200μ 500μ 1m 2m 5m 10m 20m

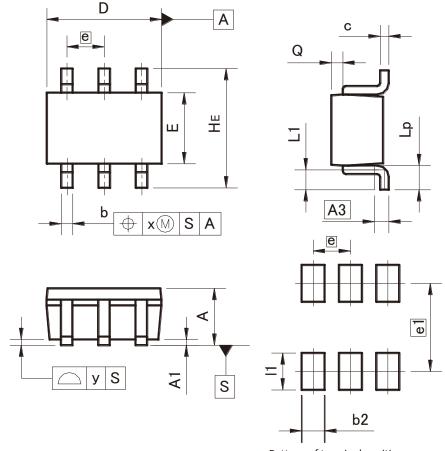
COLLECTOR CURRENT: Ic [mA]

COLLECTOR CURRENT: Ic [mA]

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●Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

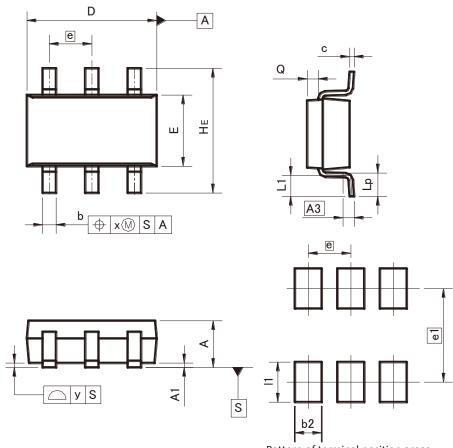
DIM MILI		ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.3	25	0.0	10
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.65		0.0	26
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
Х	_	0.10	_	0.004
У	_	0.10	_	0.004

DIM	MILIMETERS		INCHES	
DIM	MIN MAX		MIN	MAX
b2	- 0.40		_	0.016
e1	1.55		0.0	61
11	- 0.65		-	0.026

Dimension in mm / inches

●Dimensions (Unit : mm)





Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMI	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.5	25	0.0	10
b	0.25	0.40	0.010	0.016
С	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.95 0.03		37	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х	_	0.20	_	0.008
У	_	0.10	_	0.004

DIM	MILIMETERS		INCHES	
DIM	MIN MAX		MIN	MAX
b2		0.60	ı	0.024
e1	2.10		0.0	83
l1	_	0.90	_	0.035

Dimension in mm / inches

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